

BCP52; BCX52; BC52PA

60 V, 1 A PNP medium power transistors

Rev. 9 — 18 October 2011

Product data sheet

1. Product profile

1.1 General description

PNP medium power transistor series in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number ^[1]	Package			NPN complement
	NXP	JEITA	JEDEC	
BCP52	SOT223	SC-73	-	BCP55
BCX52	SOT89	SC-62	TO-243	BCX55
BC52PA	SOT1061	-	-	BC55PA

[1] Valid for all available selection groups.

1.2 Features and benefits

- High current
- Three current gain selections
- High power dissipation capability
- Exposed heatsink for excellent thermal and electrical conductivity (SOT89, SOT1061)
- Leadless very small SMD plastic package with medium power capability (SOT1061)
- AEC-Q101 qualified

1.3 Applications

- Linear voltage regulators
- High-side switches
- Battery-driven devices
- Power management
- MOSFET drivers
- Amplifiers

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{CE0}	collector-emitter voltage	open base	-	-	-60	V
I_C	collector current		-	-	-1	A
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-	-2	A

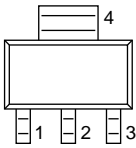
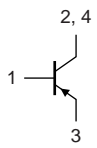
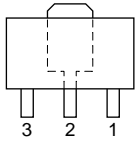
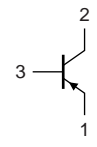
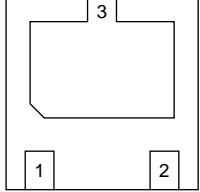
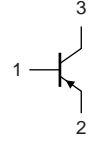


Table 2. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
h_{FE}	DC current gain	$V_{CE} = -2\text{ V};$ $I_C = -150\text{ mA}$	63	-	250	
	h_{FE} selection -10	$V_{CE} = -2\text{ V};$ $I_C = -150\text{ mA}$	63	-	160	
	h_{FE} selection -16	$V_{CE} = -2\text{ V};$ $I_C = -150\text{ mA}$	100	-	250	

2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
SOT223			
1	base		 <p style="text-align: center;"><i>sym028</i></p>
2	collector		
3	emitter		
4	collector		
SOT89			
1	emitter		 <p style="text-align: center;"><i>006aaa231</i></p>
2	collector		
3	base		
SOT1061			
1	base	 <p style="text-align: center;">Transparent top view</p>	 <p style="text-align: center;"><i>sym013</i></p>
2	emitter		
3	collector		

3. Ordering information

Table 4. Ordering information

Type number ^[1]	Package		
	Name	Description	Version
BCP52	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223
BCX52	SC-62	plastic surface-mounted package; exposed die pad for good heat transfer; 3 leads	SOT89
BC52PA	HUSON3	plastic thermal enhanced ultra thin small outline package; no leads; 3 terminals; body 2 × 2 × 0.65 mm	SOT1061

[1] Valid for all available selection groups.

4. Marking

Table 5. Marking codes

Type number	Marking code
BCP52	BCP52
BCP52-10	BCP52/10
BCP52-16	BCP52/16
BCX52	AE
BCX52-10	AG
BCX52-16	AM
BC52PA	BS
BC52-10PA	BT
BC52-16PA	BU

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit			
V_{CBO}	collector-base voltage	open emitter	-	-60	V			
V_{CEO}	collector-emitter voltage	open base	-	-60	V			
V_{EBO}	emitter-base voltage	open collector	-	-5	V			
I_C	collector current		-	-1	A			
I_{CM}	peak collector current	single pulse; $t_p \leq 1$ ms	-	-2	A			
I_B	base current		-	-0.3	A			
I_{BM}	peak base current	single pulse; $t_p \leq 1$ ms	-	-0.3	A			
P_{tot}	total power dissipation	$T_{amb} \leq 25$ °C						
			BCP52	[1]	-	0.65	W	
				[2]	-	1.00	W	
				[3]	-	1.35	W	
			BCX52	[1]	-	0.50	W	
				[2]	-	0.95	W	
				[3]	-	1.35	W	
			BC52PA	[1]	-	0.42	W	
				[2]	-	0.83	W	
				[3]	-	1.10	W	
				[4]	-	0.81	W	
				[5]	-	1.65	W	
			T_j	junction temperature		-	150	°C
			T_{amb}	ambient temperature		-55	+150	°C
			T_{stg}	storage temperature		-65	+150	°C

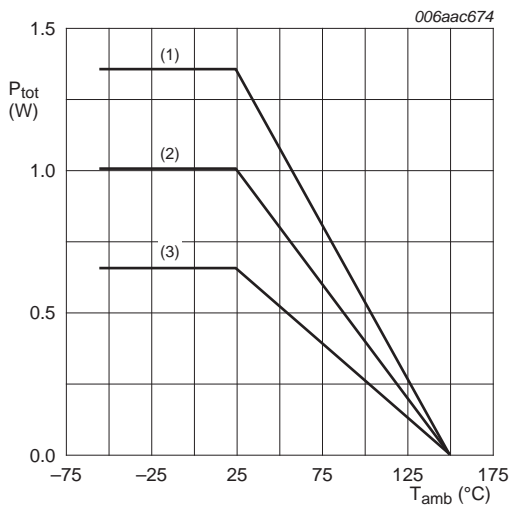
[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

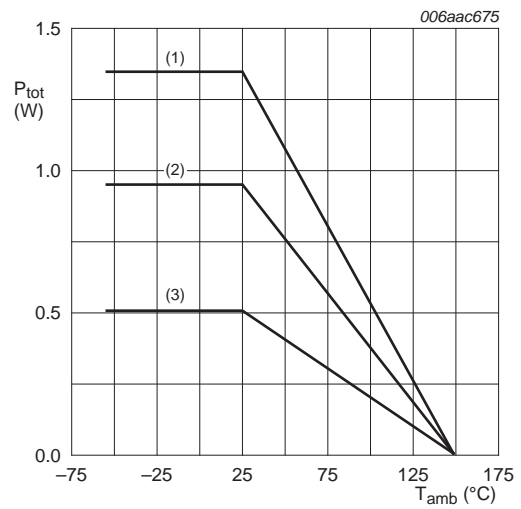
[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig 1. Power derating curves SOT223



- (1) FR4 PCB, mounting pad for collector 6 cm²
- (2) FR4 PCB, mounting pad for collector 1 cm²
- (3) FR4 PCB, standard footprint

Fig 2. Power derating curves SOT89



- (1) FR4 PCB, 4-layer copper, mounting pad for collector 1 cm²
- (2) FR4 PCB, single-sided copper, mounting pad for collector 6 cm²
- (3) FR4 PCB, single-sided copper, mounting pad for collector 1 cm²
- (4) FR4 PCB, 4-layer copper, standard footprint
- (5) FR4 PCB, single-sided copper, standard footprint

Fig 3. Power derating curves SOT1061

6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit							
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	BCP52	[1]	-	-	192	K/W					
				[2]	-	-	125	K/W					
				[3]	-	-	93	K/W					
			BCX52	[1]	-	-	250	K/W					
				[2]	-	-	132	K/W					
				[3]	-	-	93	K/W					
			BC52PA	[1]	-	-	298	K/W					
				[2]	-	-	151	K/W					
				[3]	-	-	114	K/W					
	[4]	-		-	154	K/W							
	[5]	-		-	76	K/W							
	$R_{th(j-sp)}$	thermal resistance from junction to solder point											
									BCP52	-	-	16	K/W
									BCX52	-	-	16	K/W
									BC52PA	-	-	20	K/W

[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for collector 6 cm².

[4] Device mounted on an FR4 PCB, 4-layer copper, tin-plated and standard footprint.

[5] Device mounted on an FR4 PCB, 4-layer copper, tin-plated, mounting pad for collector 1 cm².



Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT223; typical values



Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT223; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig 6. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT223; typical values



FR4 PCB, standard footprint

Fig 7. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT89; typical values



FR4 PCB, mounting pad for collector 1 cm²

Fig 8. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT89; typical values



FR4 PCB, mounting pad for collector 6 cm²

Fig 9. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT89; typical values



FR4 PCB, single-sided copper, standard footprint

Fig 10. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values



FR4 PCB, single-sided copper, mounting pad for collector 1 cm²

Fig 11. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values



FR4 PCB, single-sided copper, mounting pad for collector 6 cm²

Fig 12. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values



FR4 PCB, 4-layer copper, standard footprint

Fig 13. Transient thermal impedance from junction to ambient as a function of pulse duration for SOT1061; typical values



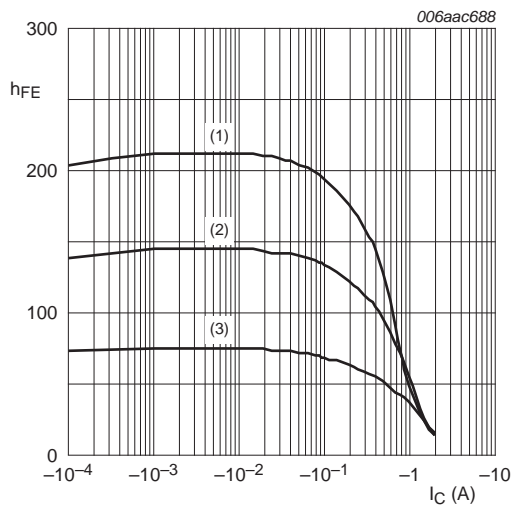
7. Characteristics

Table 8. Characteristics

T_{amb} = 25 °C unless otherwise specified.

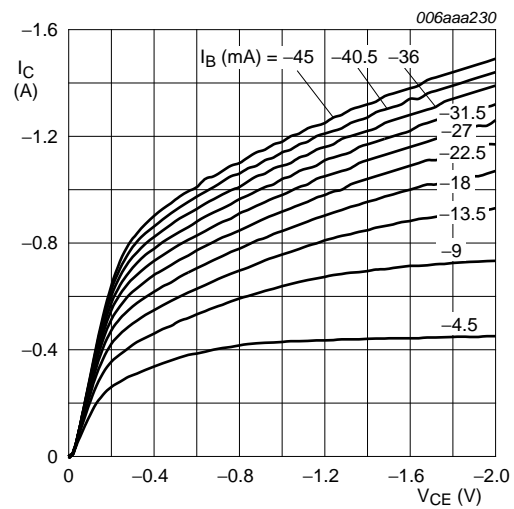
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
I _{CBO}	collector-base cut-off current	V _{CB} = -30 V; I _E = 0 A	-	-	-100	nA
		V _{CB} = -30 V; I _E = 0 A; T _j = 150 °C	-	-	-10	μA
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A	-	-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V				
		I _C = -5 mA	63	-	-	
		I _C = -150 mA	63	-	250	
		I _C = -500 mA	[1] 40	-	-	
	DC current gain	V _{CE} = -2 V				
	h _{FE} selection -10	I _C = -150 mA	63	-	160	
	h _{FE} selection -16	I _C = -150 mA	100	-	250	
V _{CEsat}	collector-emitter saturation voltage	I _C = -500 mA; I _B = -50 mA	[1] -	-	-0.5	V
V _{BE}	base-emitter voltage	V _{CE} = -2 V; I _C = -500 mA	[1] -	-	-1	V
C _C	collector capacitance	V _{CB} = -10 V; I _E = i _e = 0 A; f = 1 MHz	-	15	-	pF
f _T	transition frequency	V _{CE} = -5 V; I _C = -50 mA; f = 100 MHz	-	145	-	MHz

[1] Pulse test: t_p ≤ 300 μs; δ = 0.02.



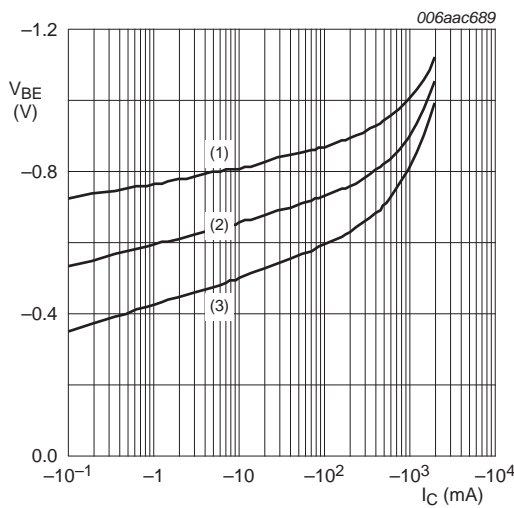
$V_{CE} = -2\text{ V}$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 15. DC current gain as a function of collector current; typical values



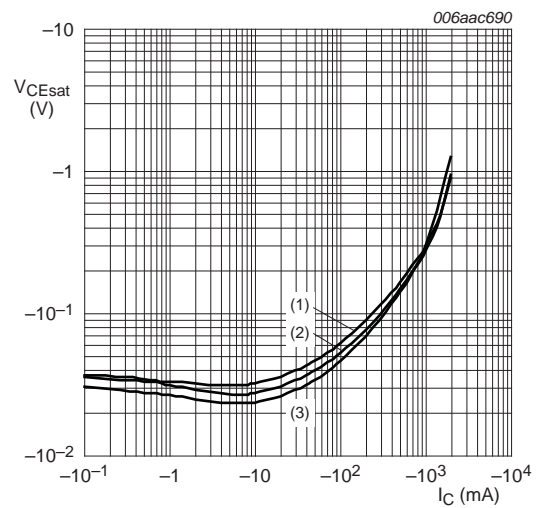
$T_{amb} = 25\text{ °C}$

Fig 16. Collector current as a function of collector-emitter voltage; typical values



$V_{CE} = -2\text{ V}$
 (1) $T_{amb} = -55\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = 100\text{ °C}$

Fig 17. Base-emitter voltage as a function of collector current; typical values



$I_C/I_B = 10$
 (1) $T_{amb} = 100\text{ °C}$
 (2) $T_{amb} = 25\text{ °C}$
 (3) $T_{amb} = -55\text{ °C}$

Fig 18. Collector-emitter saturation voltage as a function of collector current; typical values

8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

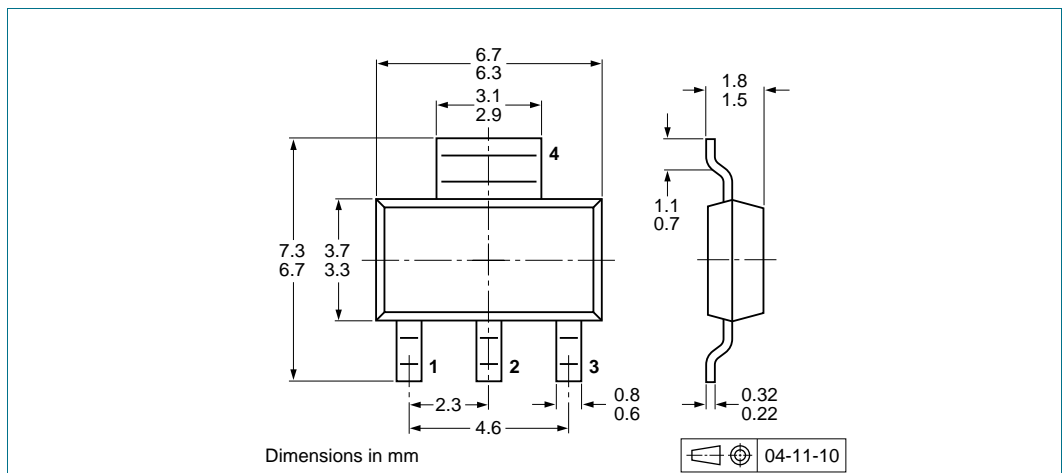


Fig 19. Package outline SOT223 (SC-73)

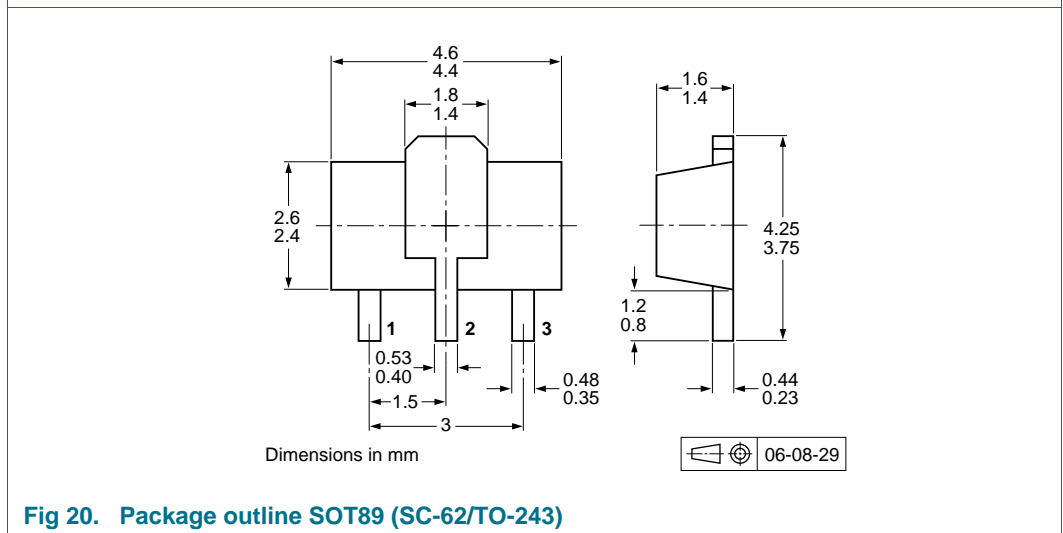


Fig 20. Package outline SOT89 (SC-62/TO-243)



Fig 21. Package outline SOT1061 (HUSON3)

10. Packing information

Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.^[1]

Type number ^[2]	Package	Description	Packing quantity		
			1000	3000	4000
BCP52	SOT223	8 mm pitch, 12 mm tape and reel	-115	-	-135
BCX52	SOT89	8 mm pitch, 12 mm tape and reel; T1 ^[3]	-115	-	-135
		8 mm pitch, 12 mm tape and reel; T3 ^[4]	-146	-	-
BC52PA	SOT1061	4 mm pitch, 8 mm tape and reel	-	-115	-

[1] For further information and the availability of packing methods, see [Section 14](#).

[2] Valid for all available selection groups.

[3] T1: normal taping

[4] T3: 90° rotated taping

11. Soldering



Fig 22. Reflow soldering footprint SOT223 (SC-73)

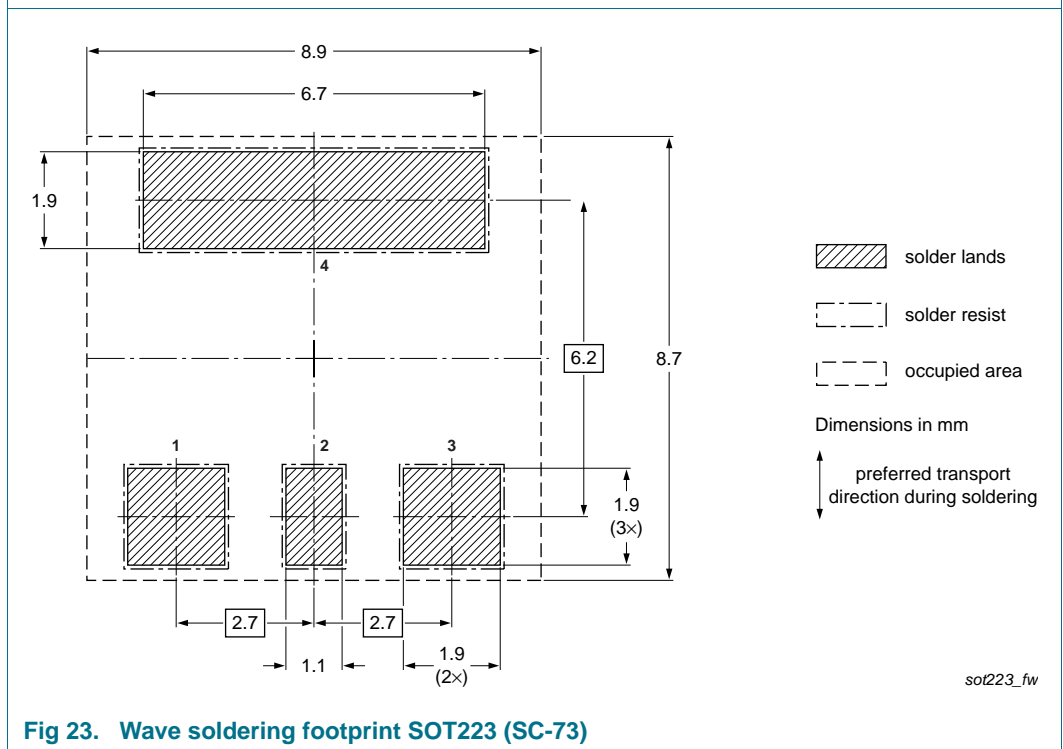


Fig 23. Wave soldering footprint SOT223 (SC-73)

